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APPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/501,516	07/14/2004	Graham Cross	CH920010024US1 6389 (8728-698)		
46069	7590 07/06/2006	EXAMINER			
F. CHAU & ASSOCIATES, LLC 130 WOODBURY ROAD			PHAM, THANHHA S		
	Y, NY 11797		ART UNIT	PAPER NUMBER	
	,		2813		

DATE MAILED: 07/06/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No	<b>).</b>	Applicant(s)	
		10/501,516		CROSS ET AL.	
Office Action Su	immary	Examiner		Art Unit	
		Thanhha Pham		2813	
The MAILING DATE of Period for Reply	this communication app	pears on the cov	er sheet with the c	orrespondence ad	dress
A SHORTENED STATUTOR WHICHEVER IS LONGER, F - Extensions of time may be available ur after SIX (6) MONTHS from the mailing - If NO period for reply is specified above - Failure to reply within the set or extend Any reply received by the Office later the	ROM THE MAILING D. der the provisions of 37 CFR 1.1 date of this communication. e, the maximum statutory period very period for reply will, by statute than three months after the mailing	ATE OF THIS C 36(a). In no event, ho will apply and will expire, cause the application	OMMUNICATION wever, may a reply be time e SIX (6) MONTHS from to become ABANDONEI	I.  lely filed  the mailing date of this of  (35 U.S.C. § 133).	
Status					
<ul> <li>1) ⊠ Responsive to commur</li> <li>2a) ☐ This action is FINAL.</li> <li>3) ☐ Since this application is closed in accordance w</li> </ul>	2b)⊠ This in condition for allowa	s action is non-fi nce except for f	ormal matters, pro		e merits is
Disposition of Claims					
4) ☐ Claim(s) 1-56 is/are pe 4a) Of the above claim( 5) ☐ Claim(s) is/are a 6) ☐ Claim(s) 1-35 and 40-4 7) ☐ Claim(s) 36-39,48-51 a 8) ☐ Claim(s) are sub  Application Papers  9) ☐ The specification is objection in the drawing(s) filed on Applicant may not reques	s) is/are withdray llowed.  7, 52-55 is/are rejected to a size objected to ject to restriction and/outside to by the Examine is/are: a) □ acc	wn from conside  I.  D.  Or election requir  er.  eepted or b) \[ \sum o	ement. bjected to by the B		
Replacement drawing she	• •	•			
Priority under 35 U.S.C. § 119		Addition (10to to			, _ , _ ,
12) Acknowledgment is made a) All b) Some * c) Certified copies of the certifi	☐ None of:  of the priority document  of the priority document  tified copies of the priorith  the International Burea	ts have been red ts have been red rity documents u (PCT Rule 17	ceived. ceived in Applicati have been receive 2(a)).	on No ed in this National	Stage
Attachment(s)  1) Notice of References Cited (PTO-8 2) Notice of Draftsperson's Patent Dr. 3) Information Disclosure Statement(s Paper No(s)/Mail Date	awing Review (PTO-948)	_	Interview Summary Paper No(s)/Mail Da Notice of Informal P Other:	ate	0-152)

#### **DETAILED ACTION**

This Office Action is in response to Applicant's Preliminary Amendment dated 7/14/2004.

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 1. Claims 31-35, 40-42 and 52-55 are rejected under 35 U.S.C. 102(b) as being anticipated by or, in the alternative, under 35 U.S.C. 103(a) as obvious over Niederman et al [US 5,994,160].
- ▶ With respect to claims 31, 34-35, Niedermann et al (figs 1-9, cols 1-11) discloses the claimed method forming a microstructure, comprising:

depositing a seed material (col 8 lines 8-11: fine diamond particles) on a substrate (8c, silicon, fig 4D);

growing a nanotube (diamond tip 3c, fig 4D, col 8 lines from the seed material; depositing microstructure material (24b, fig 4D, col 8 lines 12-20) on the substrate to embed the nanotube in the microstructure material; and

detaching the substrate to release the microstructure (figs 4D-4G).

- ▶ With respect to claim 32, the microstructure material (24b, fig 4D) would be shaped prior to the step of detaching the substrate to release the microstructure (fig 4G)
- ► With respect to claim 40, Niedermann et al (col 8 lines 12-20) discloses growing of the nanotube comprises: heating the substrate in vacuum conditions; and applying a field to the substrate (plasma deposition would be practiced in heating, vacuum conditions an applying a field)
- ▶ With respect to claims 41-42, parameters for growing the nanotube is considered to involve routine optimization while has been held to be within the level of ordinary skill in the art. As noted in In re Aller 105 USPQ233, 255 (CCPA 1955)., the selection of reaction parameters such as temperature and concentration would have been obvious.

"Normally, it is to be expected that a change in temperature, or in concentration, or in both, would be an unpatentable modification. Under some circumstances, however, changes such as these may be impart patentability to a process if the particular ranges claimed produce a new and unexpected result which is different in kind and not merely degree from the results of the prior art...such ranges are termed "critical ranges and the applicant has the burden of proving such criticality... More particularly, where the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation."

See also In re Waite 77 USPQ 586 (CCPA 1948); In re Scherl 70 USPQ 204 (CCPA 1946); In re Irmscher 66 USPQ 314 (CCPA 1945); In re Norman 66

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USPQ 308 (CCPA 1945); In re Swenson 56 USPQ 372 (CCPA 1942); In re Sola 25 USPQ 433 (CCPA 1935); In re Dreyfus 24 USPQ 52 (CCPA 1934).

- With respect to claims 52-53, Niedermann et al (figs 4B-4C, col 7-8) shows depositing of the seed material comprises: depositing a photoresist layer on the substrate; forming an aperture in the photoresist layer wherein forming of the aperture comprise under-etching the photoresist layer to produce a cavity in the photoresist layer (developing photorsist layer); masking the substrate with the photoresist layer (22c) to locate the seed material at a site on the substrate defined by the aperture; and removing the photoresist layer to remove surplus seed material.
- ▶ With respect to claim 54-55, Niedermann et al (figs 4B-4C, col 7-8 & col 5 lines 36-60) shows forming a tip image (13c, fig 4B) in the substrate to produce a mold for receiving the microstructure material wherein forming of the tip image comprises: depositing a photoresist layer on the substrate; forming an aperture in the photoresist layer; and under etching the substrate beneath the photoresist layer to create the tip image (photo etch using mask − col 5 lines 38-60).

#### Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

2. Claims 43-47 are rejected under 35 U.S.C. 103(a) as being unpatentable over Niedermann et al [US 5,994,160] in view of Matsui et al [US 6,960,334].

Niedermann et al substantially discloses the claimed method including using plasma to grow nanotube, Niederman et al does not expressly mention about using electric field or magnetic field for plasma growing or deposition technique.

However, applying electric field or magnetic field are known technique of plasma deposition/growing. See Matsui et al as an evident that shows using electric field or magnetic field in plasma depositing/growing nanotubes.

Therefore, at the time of invention, in view of Matsui et al, it would have been obvious for those skill in the art to modify process of Niedermann et al by using the electric field or magnetic field as being claimed to efficiently growing the nanotube for microstructure.

#### Allowable Subject Matter

3. Claims 36-39, 48-51 and 56 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanhha Pham whose telephone number is (571) 272-

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1696. The examiner can normally be reached on Monday and Thursday 9:00AM - 9:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

THANHHA S. PHAM PRIMARY EXAMINER